Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	63	(US-20030085195-\$ or US-20040045502-\$ or US-20010004878-\$ or US-20010009156-\$ or	US-PGPUB; USPAT;	OR	ON	2006/03/19 16:03
		US-20040258848-\$ or US-20050208774-\$ or US-20020117188-\$).did. or (US-6780277-\$ or US-6851436-\$ or US-6592678-\$ or US-6287390-\$ or US-6253775-\$ or	EPO; JPO; DERWENT			
10		US-6203627-\$ or US-6158447-\$ or US-5715173-\$ or US-5693148-\$ or US-4710261-\$ or US-3664354-\$ or US-6210481-\$ or US-6293288-\$ or US-6001215-\$ or	*****			
		US-5482068-\$ or US-5817185-\$ or US-3620813-\$ or US-4892761-\$ or US-4616306-\$ or US-5672230-\$ or US-3559557-\$ or US-4966094-\$ or US-5845660-\$ or US-6131588-\$ or US-6945258-\$).did. or		a a		
		(DE-10145186-\$).did. or (JP-2004296506-\$ or JP-2003338488-\$ or JP-2000218474-\$ or JP-11054586-\$ or JP-10318905-\$ or JP-08067413-\$ or JP-07295232-\$ or		e de la companya de l La companya de la co		
	- , , , , , , , , , , , , , , , , , , ,	JP-64000743-\$ or JP-2003086479-\$ or JP-11090871-\$ or JP-2003151950-\$ or JP-10247679-\$ or JP-11329955-\$ or JP-03070154-\$).did. or (KR-2005008064-\$ or DE-10145186-\$ or KR-2001036434-\$ or JP-2000218474-\$ or JP-11123479-\$ or			7, 33 14	
	4, ·	EP-805481-\$ or JP-08067413-\$ or JP-64000743-\$ or US-6851436-\$ or JP-2004031572-\$ or US-20030046034-\$ or GB-2316780-\$ or JP-08195368-\$ or JP-59036956-\$ or JP-07283129-\$).did.				
L2	30	1 and (shutter closure door gate valve)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/19 16:45
L3	51	118/668.ccls. and ((count\$3 number quantity) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 16:20
L4	3	118/668.ccls. and ((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (batch cassette container bath))	US-PGPUB; USPAT	OR	ON	2006/03/19 16:20
L5	3	118/668.ccls. and ((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (batch cassette container bath tank pod))	US-PGPUB; USPAT	OR	ON	2006/03/19 16:20
L6	0	1 and (camera "ccd")	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/19 16:45
S7	161	((156/345.15) or (156/345.16)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/19 06:54
S8	51	S7 and ((count\$3 number) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 16:20
S9	1341	((156/345.15) or (156/345.16) or (118/429)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/18 22:54
S10	117	(S9 S7) and ((count\$3 number) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/18 22:55
S11 -	24	(\$9 \$7) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:42
S12	23	(S9 S7) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (time duration))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:42
S13	7	("4710261"   "4871417"   "5332445"   "5414259"   "5779927"   "5820689"   "6001215").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/18 23:01
S14	0	("6780277").URPN.	USPAT	OR	ON	2006/03/18 23:03

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S15	50982	(c23f001\$.ipc. h01l021\$.ipc. b05c003\$.ipc. b05c019\$.ipc.) and ((count\$3 number) and (substrate wafer semiconductor workpiece) and (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3 tim\$3 duration))	US-PGPUB; USPAT	OR	ON	2006/03/18 23:15
S16	24	(S9 S7) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (tim\$3 duration))	US-PGPUB; USPAT	OR	ON	2006/03/18 23:15
S17	1	S16 not S12	US-PGPUB; USPAT	OR	ON	2006/03/18 23:15
\$18	14040	(c23f001\$.ipc. h01l021\$.ipc. b05c003\$.ipc. b05c019\$.ipc.) and ((count\$3 number) and (substrate wafer semiconductor workpiece) and (determin\$3 sens\$3 detect\$3 measur\$4	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:16
S19	3666	acquir\$3 tim\$3 duration))  (c23f001\$.ipc. h01l021\$.ipc. b05c003\$.ipc. b05c019\$.ipc.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3 tim\$3 duration))	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:17
S20	281	(c23f001\$.ipc. h01l021\$.ipc. b05c003\$.ipc. b05c019\$.ipc.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (tim\$3 duration))	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:18
S21	28	(c23f001\$.ipc. h01l021\$.ipc. b05c003\$.ipc. b05c019\$.ipc.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (tim\$3 duration)) and (etch\$3)	EPO; JPO; DERWENT	OR	ON .	2006/03/18 23:27
<b>S22</b>	2	"08064413"	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:24
523	2	"08067413"	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:25
S24	1	"03172637"	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:26
S25	2	"3172637"	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:26
S26	30	((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (tim\$3 duration)) and (etch\$3)	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:27
S27	55	((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (tim\$3 duration)) and (etch\$3)	EPO; JPO; DERWENT	OR	ON .	2006/03/18 23:33
S28	27	S27 not S21	EPO; JPO; DERWENT	OR	ON	2006/03/18 23:28
S29	226	((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (tim\$3 duration) with (treat\$4	EPO; JPO; DERWENT	OR	ON	2006/03/19 00:18
<b>S30</b>	1689	process\$4))  FURUKAWA-TAKAHIRO.in. KITAHARA-SHIGENORI.in.  IWAZU-HARUO.in. matsumoto-takashi.in. hirayama-tsukasa.in.	EPO; JPO; DERWENT	OR	ON	2006/03/19 00:27
S31	238	FURUKAWA-TAKAHIRO.in. KITAHARA-SHIGENORI.in. IWAZU-HARUO.in. matsumoto-takashi.in. hirayama-tsukasa.in.	US-PGPUB; USPAT	OR	ON	2006/03/19 00:28
532	57	S31 and quantity	US-PGPUB; USPAT	OR	ON * · *	2006/03/19 00:31
S33	238	S31	US-PGPUB; USPAT	OR	ON	2006/03/19 00:31
S34	178	S31 and (number count\$3 quantity)	US-PGPUB; USPAT	OR	ON	2006/03/19 00:32
S35	31	S31 and ((number count\$3 quantity) with (wafer substrate semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:33
536	. 238	FURUKAWA-TAKAHIRO.in. KITAHARA-SHIGENORI.in. IWAZU-HARUO.in. matsumoto-takashi.in. hirayama-tsukasa.in.	US-PGPUB; USPAT	OR	ON	2006/03/19 00:33
	L		l	<u>Ц</u>	1	<u> </u>

<b>S</b> 37	31	S36 and ((number count\$3 quantity) with (wafer substrate semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:33
S38	472	("134"/\$.ccls.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (time duration))	US-PGPUB; USPAT	OR .	ON	2006/03/19 00:42
S39	390	("134"/\$.ccls.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3))	US-PGPUB; USPAT	OR -	ON	2006/03/19 00:45
S40	715	S38 S39	US-PGPUB; USPAT	OR	ON	2006/03/19 00:42
S41	617	S40 and ((time\$3 duration) with (treat\$4 process\$4 duration))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:44
S42	500	S41 and (liquid solution)	US-PGPUB; USPAT	OR	ON	2006/03/19 00:44
S43	17096	("134"/\$.ccls.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) (time\$3 duration))	US-PGPUB; USPAT	OR	ON .	2006/03/19 00:45
S44	55	("134"/\$.ccls.) and ((count\$3 number) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (time\$3 duration))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:46
S45	69	("134"/\$.ccls.) and ((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (time\$3 duration))	US-PGPUB; USPAT	OR	ON	2006/03/19 00:46
S46	59	("134"/\$.ccls.) and ((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (time\$3 duration)) and (liquid solution)	US-PGPUB; USPAT	OR	ON	2006/03/19 00:46
S47	59	("134"/\$.ccls.) and ((count\$3 number quantity) with (substrate wafer semiconductor workpiece) with (determin\$3 sens\$3 detect\$3 measur\$4 acquir\$3) with (time\$3 duration)) and (liquid solution bath)	US-PGPUB; USPAT	OR	ON	2006/03/19 00:59
S48	3	izuta-takashi.in.	US-PGPUB; USPAT	OR	ON	2006/03/19 01:00
S49	3	izuta-takashi.in.	US-PGPUB; USPAT	OR	ON	2006/03/19 01:00
S50	10	izuta-takashi.in.	EPO; JPO; DERWENT	OR	ON	2006/03/19 01:00
S51	7	"64743"	EPO; JPO; DERWENT	OR	ON	2006/03/19 01:17
S52	46	(US-20040045502-\$ or US-20030085195-\$ or US-20010009156-\$ or US-20010004878-\$).did. or (US-6780277-\$ or US-6001215-\$ or US-4710261-\$ or US-3664354-\$ or US-3620813-\$ or US-6203627-\$ or US-6210481-\$ or US-6592678-\$ or US-6253775-\$ or US-6158447-\$ or US-6293288-\$ or US-5817185-\$ or US-5482068-\$ or US-5693148-\$ or US-6851436-\$ or US-5482068-\$ or US-5715173-\$).did. or (DE-10145186-\$).did. or (JP-2003338488-\$ or JP-64000743-\$ or JP-2004296506-\$ or JP-08067413-\$ or JP-2003086479-\$ or JP-03070154-\$ or JP-10247679-\$ or JP-2003151950-\$ or JP-200218474-\$ or JP-11329955-\$ or JP-11054586-\$ or JP-11090871-\$ or JP-10318905-\$ or JP-07295232-\$).did. or (JP-2004031572-\$ or EP-805481-\$ or JP-08067413-\$ or KR-2005008064-\$ or DE-10145186-\$ or GB-2316780-\$ or KR-2001036434-\$ or	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/19 06:02
		JP-11123479-\$ or JP-07283129-\$ or JP-59036956-\$).did.		2		

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S53		(US-20040045502-\$ or US-20030085195-\$ or US-20010009156-\$ or US-20010004878-\$).did. or (US-6780277-\$ or US-6001215-\$ or US-4710261-\$ or US-3664354-\$ or US-3620813-\$ or US-6203627-\$ or US-6210481-\$ or US-6592678-\$ or US-6253775-\$ or US-6158447-\$ or US-6293288-\$ or US-5817185-\$ or US-5482068-\$ or US-5693148-\$ or US-6851436-\$ or US-6287390-\$ or US-5715173-\$).did. or (DE-10145186-\$).did. or (JP-2003338488-\$ or JP-64000743-\$ or JP-2004296506-\$ or JP-08067413-\$ or JP-2003086479-\$ or JP-03070154-\$ or JP-10247679-\$ or JP-2003151950-\$ or JP-2000218474-\$ or JP-1329955-\$ or JP-11054586-\$ or JP-11090871-\$ or JP-10318905-\$ or JP-07295232-\$).did. or (JP-2004031572-\$ or EP-805481-\$ or GB-2316780-\$ or KR-2001036434-\$ or	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/19 06:53
<b>S</b> 54	790	JP-11123479-\$ or JP-07283129-\$ or JP-59036956-\$).did. ishii-tomoyuki.in. kobayashi-kazuyoshi.in.	,US-PGPUB; USPAT;	OR	ON .	2006/03/19 06:53
			EPO; JPO; DERWENT		C-1	
S55	1	ishii-tomoyuki.in. and kobayashi-kazuyoshi.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/19 06:53
S56	.379	((156/345.15) or (156/345.16) or (156/345.11)).CCLS.	US-PGPUB; USPAT	OR	OFF	2006/03/19 13:13
S57	1	S56 and ((tim\$3 duration) with (based basing) with (count\$3 number quantitiy) with (process\$3 clean\$3 treat\$4 etch\$4))	US-PGPUB; USPAT	OR	ON	2006/03/19 06:55
S58	1	S56 and ((tim\$3 duration) with (based basing) with (count\$3 number quantity) with (process\$3 clean\$3 treat\$4 etch\$4))	US-PGPUB; USPAT	OR	ON	2006/03/19 13:14
S59	8454	((tim\$3 duration) with (based basing) with (count\$3 number quantity) with (process\$3 dean\$3 treat\$4 etch\$4))	US-PGPUB; USPAT	OR	ON	2006/03/19 06:56
S60	1571	156/345.1-345.23.ccls.	US-PGPUB; USPAT	OR	ON	2006/03/19 13:21
S61	86	S60 and ((tim\$3 duration) with (count\$3 number quantity) with (process\$3 clean\$3 treat\$4 etch\$4) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 13:16
S62	90	S60 and ((tim\$3 duration period length) with (count\$3 number quantity) with (process\$3 clean\$3 treat\$4 etch\$4) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 13:21
S63	. 51	(US-20040045502-\$ or US-20030085195-\$ or US-20010009156-\$ or US-20010004878-\$).did. or (US-6780277-\$ or US-6001215-\$ or US-4710261-\$ or US-3664354-\$ or US-3620813-\$ or US-6203627-\$ or US-6210481-\$ or US-6592678-\$ or US-6253775-\$ or US-6158447-\$ or US-6293288-\$ or US-5817185-\$ or US-5482068-\$ or US-5693148-\$ or US-6851436-\$ or US-6287390-\$ or US-5715173-\$).did. or (DE-10145186-\$).did. or (JP-2003338488-\$ or JP-64000743-\$ or JP-2004296506-\$ or JP-08067413-\$ or JP-2003086479-\$ or JP-03070154-\$ or JP-11329955-\$ or JP-2003151950-\$ or JP-1030871-\$ or JP-1318905-\$ or JP-07295232-\$).did. or (JP-2004031572-\$ or EP-805481-\$ or JP-08067413-\$ or KR-2005008064-\$ or DE-10145186-\$ or GB-2316780-\$ or KR-2001036434-\$ or JP-1123479-\$ or JP-07283129-\$ or JP-59036956-\$ or JP-08195368-\$ or JP-2000218474-\$ or JP-64000743-\$ or US-20030046034-\$ or US-6851436-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/19 13:17
S64	3	S62 and S63	US-PGPUB; USPAT	OR	ON	2006/03/19 13:18
<b>S65</b> .	1571	156/345.1-345.23.ccls.	US-PGPUB; USPAT	OR	ON	2006/03/19 13:21

S66	90	S65 and ((tim\$3 duration period length) with (count\$3 number quantity) with (process\$3 clean\$3 treat\$4 etch\$4) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON	2006/03/19 14:21
S67	12	S65 and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) )	US-PGPUB; USPAT	OR	ON	2006/03/19 14:08
S68	84	"134"/\$.ccls. and (bath tank immers\$7) and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) )	US-PGPUB; USPAT	OR	ON	2006/03/19 13:31
S69	33	"134"/\$.ccls. and (bath tank immers\$7) and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) ) and (substrate wafer workpiece semiconductor)	US-PGPUB; USPAT	OR	ON	2006/03/19 13:50
S70	7	(bath tank immers\$7) and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) ) and (substrate wafer workpiece semiconductor)	EPO; JPO; DERWENT	OR	ON	2006/03/19 13:36
S71 `	. 0	("4892761").URPN.	USPAT	OR	ÔN ·	2006/03/19 13:44
S72	12	("2386079"   "3165108"   "3641906"   "3751223"   "3969074"   "3986518"   "4374681"   "4377986"   "4406248"   "4568576").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/19 13:44
S73	8	("4374681").URPN.	USPAT	OR	ON	2006/03/19 13:48
S74	83	("204"/\$.ccls. "205"/\$.ccls.) and (bath tank immers\$7) and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) ) and (substrate wafer workpiece semiconductor)	US-PGPUB; USPAT	OR	ON	2006/03/19 13:51
S75	44	("118"/\$.ccls.) and (bath tank immers\$7) and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) ) and (substrate wafer workpiece semiconductor)	US-PGPUB; USPAT	OR	ON	2006/03/19 13:52
S76	122	S74 S75	US-PGPUB; USPAT	OR	ON	2006/03/19 13:55
S77	26	("156"/\$.cds.) and (bath tank immers\$7) and ((program\$4 software computer "cpu" memory "ram" "rom") with (tim\$3 duration period length) with (count\$3 number quantity) ) and (substrate wafer workpiece semiconductor)	US-PGPUB; USPAT	OR	ON	2006/03/19 13:52
S78	268	S65 and ((tim\$3 duration period length) with (count\$3 number quantity) )	US-PGPUB; USPAT	OR	ON	2006/03/19 14:08
S79	4.	S65 and ((tim\$3 duration period length) with (count\$3 number quantity) with (based basing according))	US-PGPUB; USPAT	OR	ON	2006/03/19 14:10
S80	3	118/429.ccls. and ((tim\$3 duration period length) with (count\$3 number quantity) with (based basing according))	US-PGPUB; USPAT	OR	ON	2006/03/19 14:10
S81	36	156/345.\$.ccls. and ((tim\$3 duration period length) with (count\$3 number quantity) with (based basing according))	US-PGPUB; USPAT	OR	ON	2006/03/19 14:16
S82	1	("5672230").PN.	US-PGPUB; USPAT	OR	OFF	2006/03/19 14:17
S83	4	("5672230").URPN.	USPAT .	OR -	ON	2006/03/19 14:17
S84	. 4	("5672230").URPN.	USPAT	OR	ON	2006/03/19 14:18
S85	1	("5421905").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/19 14:18
S86	74	134/113.cds. and ( (count\$3 number quantity) with (substrate wafer semiconductor workpiece))	US-PGPUB; USPAT	OR	ON .	2006/03/19 14:56
\$87 <sup>.</sup>	.1	("6780277").PN.	US-PGPUB; USPAT	OR	OFF	2006/03/19 14:56